DSA2001

Silicon PNP epitaxial planar type

For general amplification Complementary to DSC2001

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-60	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Emitter-base voltage (Collector open)	V _{EBO}	-7	V
Collector current	I _C	-100	mA
Peak collector current	I _{CP}	-200	mA
Collector power dissipation	P _C	200	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \ \mu A, I_{\rm C} = 0$	-7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -10$ V, $I_{\rm B} = 0$			-100	μΑ
Forward current transfer ratio *	$h_{\rm FE}$	$V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA	210		460	—
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -100 \text{ mA}, I_{\rm B} = -10 \text{ mA}$		- 0.2	- 0.5	V
Transition frequency	f_{T}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -2$ mA		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Code	R	S	0
Rank	R	S	No-rank
$h_{\rm FE}$	210 to 340	290 to 460	210 to 460
Marking Symbol	A1R	A1S	Al

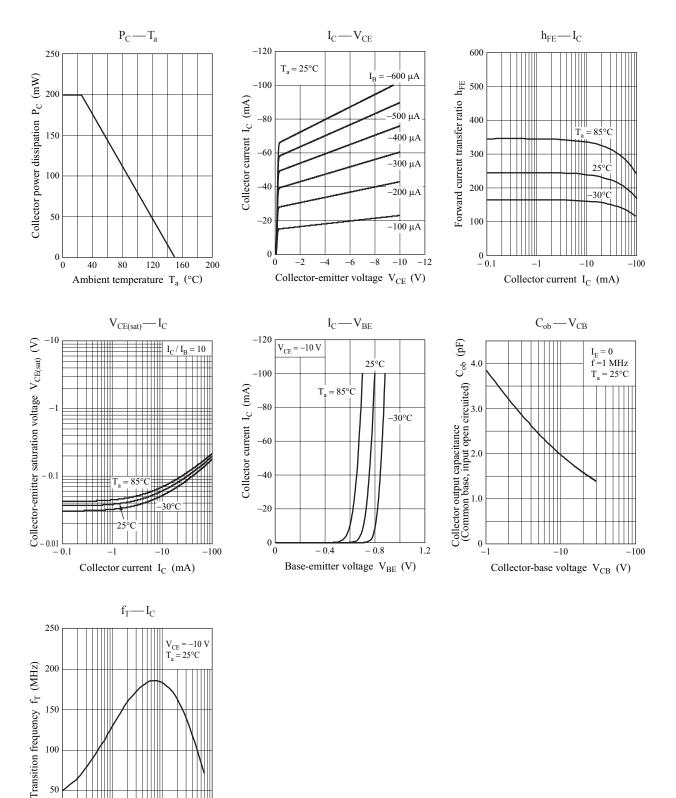
Product of no-rank is not classified and have no marking symbol for rank.

- Package
- Code
- Mini3-G3-B
- Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

Marking Symbol: A1

DSA2001

Panasonic



2

50

0

-1

Collector current I_C (mA)

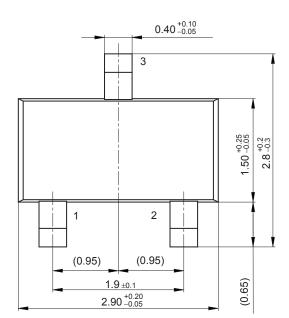
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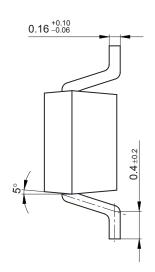
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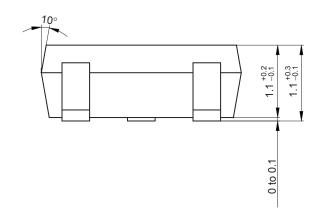
Panasonic

Mini3-G3-B

Unit: mm







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